



NPN GENERAL PURPOSE SWITCHING TRANSISTOR

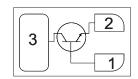
VOLTAGE 40 Volt POWER 250 mWatt

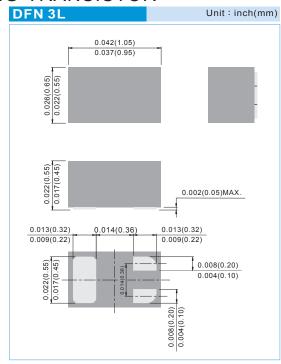
FEATURES

- · NPN epitaxial silicon, planar design
- Collector-emitter voltage VCE = 40V
- · Collector current IC = 200mA
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

MECHANICAL DATA

- · Case: DFN 3L, Plastic
- Terminals: Solderable per MIL-STD-750, Method 2026
- · Approx. Weight: 0.00004 ounces, 0.0011 grams
- · Marking: AC





ABSOLUTE RATINGS

Parameter	Symbol	Value	Units	
Collector - Emitter Voltage	VCEO	40	V	
Collector - Base Voltage	Vсво	60	V	
Emitter - Base Voltage	VEBO	6.0	V	
Collector Current - Continuous	Ic	200	mA	

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Units
Max Power Dissipation (Note 1)	Ртот	250	mW
Thermal Resistance , Junction to Ambient	RθJA	500	°C/W
Junction Temperature	TJ	-55 to +150	°C
Operating Temperature	Тѕтс	-55 to +150	°C

Note 1: Transistor mounted on FR-4 board 70 x 60 x 1mm.

PAN JIT RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE



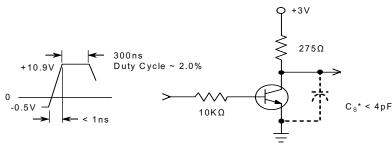


ELECTRICAL CHARACTERISTICS

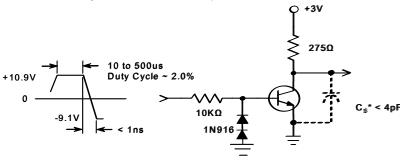
Parameter	Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Collector - Emitter Breakdown Voltage	V _(BR) CEO	IC=1.0mA, IB=0	40	-	-	V
Collector - Base Breakdown Voltage	V _(BR) CBO	IC=10uA, IE=0	60	-	-	٧
Emitter - Base Breakdown Voltage	V _(BR) EBO	IE=10uA, IC=0	6.0	-	-	٧
Base Cutoff Current	Івс	VCE=30V, VEB=3.0V	-	-	50	nA
Collector Cutoff Current	Icex	VCE=30V, VEB=3.0V	-	-	50	nA
DC Current Gain (Note 2)	h _{FE}	IC=0.1mA, VCE=1.0V IC=1.0mA, VCE=1.0V IC=10mA, VCE=1.0V IC=50mA, VCE=1.0V IC=100mA, VCE=1.0V	40 70 100 60 30	- - - -	- - 300 - -	-
Collector - Emitter Saturation Voltage (Note 2)	VCE(SAT)	IC=10mA, IB=1.0mA IC=50mA, IB=5.0mA	-	-	0.2 0.3	٧
Base - Emitter Saturation Voltage (Note 2)	VBE(SAT)	IC=10mA, IB=1.0mA IC=50mA, IB=5.0mA	0.65	-	0.85 0.95	>
Collector - Base Capacitance	Ссво	VCB=5V, IE=0, f=1MHz	-	-	4.0	pF
Emitter - Base Capacitance	Сево	VEB=0.5V, IC=0, f=1MHz	-	-	8.0	pF
Delay Time	td	VCC=3V,VBE=0.5V, IC=10mA,IB=1.0mA	-	-	35	ns
Rise Time	tr	VCC=3V,VBE=0.5V, IC=10mA,IB=1.0mA	-	-	35	ns
Storage Time	ts	VCC=3V,IC=10mA IB1=IB2=1.0mA	-	-	200	ns
Fall Time	tf	VCC=3V,IC=10mA IB1=IB2=1.0mA	-	-	50	ns

Note 2: Pulse Test: Pulse Width < 300 us, Duty Cycle < 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS



Delay and Rise Time Equivalent Test Circuit

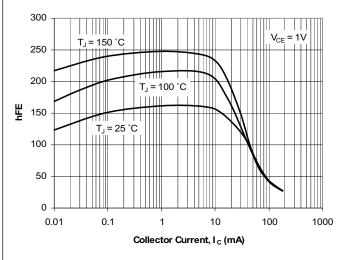


Storage and Fall Time Equivalent Test Circuit









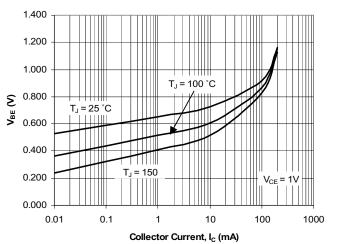
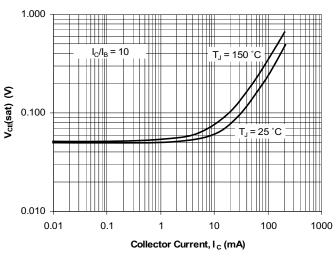


Fig. 1. Typical h_{FE} vs Collector Current

Fig. 2. Typical V_{BE} vs Collector Current



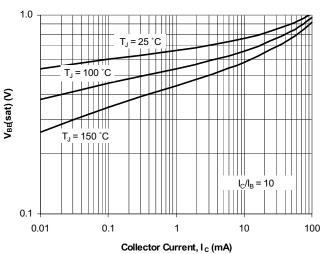


Fig. 3. Typical V_{CE} (sat) vs Collector Current

Fig. 4. Typical V_{BE} (sat) vs Collector Current

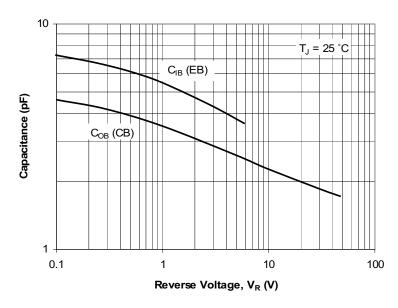
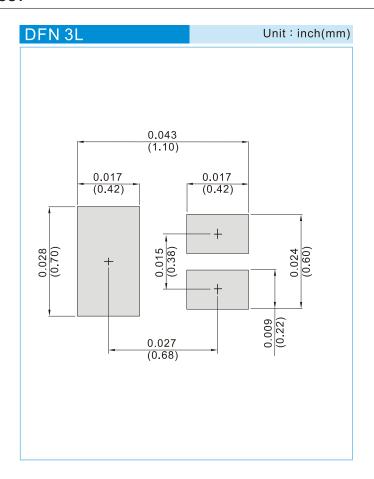


Fig. 5. Typical Capacitances vs Reverse Voltage





MOUNTING PAD LAYOUT



ORDER INFORMATION

· Packing information

T/R - 8K per 7" plastic Reel





Part No_packing code_Version

MMBT3904FN3_R1_00001

For example:



Packing Code XX			Version Code XXXXX			
Packing type	1 st Code	Packing size code	2 nd Code	HF or RoHS	1st Code	2 nd ~5 th Code
Tape and Ammunition Box (T/B)	Α	N/A	0	HF	0	serial number
Tape and Reel (T/R)	R	7"	1	RoHS	1	serial number
Bulk Packing (B/P)	В	13"	2			
Tube Packing (T/P)	Т	26mm	X			
Tape and Reel (Right Oriented) (TRR)	S	52mm	Y			
Tape and Reel (Left Oriented) (TRL)	L	PANASERT T/B CATHODE UP (PBCU)	U			
FORMING	F	PANASERT T/B CATHODE DOWN (PBCD)	D			





Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties
 of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation.
 Customers are responsible in comprehending the suitable use in particular applications.
 Panjit International Inc. makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Panjit manufacturer:

Other Similar products are found below:

004419CB 013607A 039866A 062330D 067289D 068071B 069120X 098342B 098733E 12A02CH-TL-E 12A02MH-TL-E 15C01C-TB-E 15C01M-TL-E 15C01SS-TL-E 15C02CH-TL-E 15C02MH-TL-E 15GN01MA-TL-E 15GN03CA-TB-E 15GN03FA-TL-H 15GN03MA-TL-E 2DA1201Y-7 2DA1201YQTC 2DA1213O-13 2DA1213YQ-13 2DA1774Q-7-F 2DA1774QLP-7 2DA1774QLP-7B 2DA1774R-7-F 2DA1797-13 2DA1971-7 2DA2018-7 2DB1132Q-13 2DB1132R-13 2DB1184Q-13 2DB1188Q-13 2DB1188R-13 2DB1386Q-13 2DB1386R-13 2DB1424R-13 2DB1689-7 2DB1694-7 2DB1697-13 2DB1713-13 2DB1714-13 2DC2412R-7 2DC4617Q-7-F 2DC4617QLP-7B 2DC4617S-7-F 2DC4672-13 2DD1664P-13